

What is claimed is:

1. A method of manufacturing an active matrix display device wherein said display device has a first substrate provided with a plurality of pixel electrodes and switching thin film transistors, the method comprising the steps of:

forming a semiconductor film over a glass substrate;

crystallizing said semiconductor film;

patterning the crystallized semiconductor film into a plurality of semiconductor islands;

forming a plurality of thin film transistors using said semiconductor islands;

forming a driver circuit with said plurality of thin film transistors;

attaching said glass substrate provided with said driver circuit to said first substrate.

2. A method of manufacturing a display device comprising:

preparing at least one display substrate provided with electrodes;

forming a semiconductor film over a glass substrate;

crystallizing said semiconductor film;

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forming a semiconductor film over a glass substrate;
crystallizing said semiconductor film;
patterning the crystallized semiconductor film into a
plurality of semiconductor islands;

dividing said glass substrate to obtain at least one divided glass substrate wherein said divided glass substrate carries at least one of said driver circuits thereon; and

attaching said divided glass substrate to a display substrate so that said driver circuit is electrically connected to said electrodes.

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8. A method according to claim 6 further comprising a step of removing the divided glass substrate from said display substrate.

9. A method of manufacturing an active matrix type display device comprising:

preparing at least one display substrate provided with a plurality of pixel electrodes and switching thin film transistors for switching said pixel electrodes;

forming a semiconductor film over a glass substrate;

crystallizing said semiconductor film;

patterning the crystallized semiconductor film into a plurality of semiconductor islands;

forming a plurality of thin film transistors with said semiconductor islands as an active layer thereof for constituting a plurality of driver circuits;

dividing said glass substrate to obtain at least one divided glass substrate wherein said divided glass substrate carries at least one of said driver circuits thereon; and

attaching said divided glass substrate to a display substrate so that said driver circuit is operationally connected to said switching thin film transistors.

10. A method according to claim 9 further comprising a step of removing the divided glass substrate from said display substrate.

11. A method according to claim 9 wherein a thickness of said semiconductor islands is from 400 to 600Å.

12. A method of manufacturing an active matrix type display device comprising:

preparing at least one display substrate provided with a plurality of pixel electrodes and switching thin film transistors for switching said pixel electrodes

forming a semiconductor film over a glass substrate;

crystallizing said semiconductor film wherein the crystallization is promoted by adding a catalyst to said semiconductor film;

patterning the crystallized semiconductor film into a plurality of semiconductor islands;

forming a plurality of thin film transistors with said semiconductor islands as an active layer thereof for constituting a plurality of driver circuits;

dividing said glass substrate to obtain at least one divided glass substrate wherein said divided glass

substrate carries at least one of said driver circuits thereon; and

attaching said divided glass substrate to a display substrate so that said driver circuit is operationally connected to said switching thin film transistors.

13. A method according to claim 12 further comprising a step of removing the divided glass substrate from said display substrate.

14. A method according to claim 12 wherein a thickness of said semiconductor islands is from 400 to 600Å.

15. A method according to claim 12 wherein said catalyst comprises nickel.

16. A method of manufacturing a display device comprising:

preparing at least one display substrate provided with a plurality of first electrodes;

forming a semiconductor film over a glass substrate;

crystallizing said semiconductor film;

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patterning the crystallized semiconductor film into a plurality of semiconductor islands;

forming a plurality of thin film transistors with said semiconductor islands as an active layer thereof for constituting a plurality of driver circuits;

forming a passivation film over the plurality of thin film transistors;

forming transparent electrodes over said passivation film wherein said transparent electrodes comprise a transparent conductive oxide;

dividing said glass substrate to obtain at least one divided glass substrate wherein said divided glass substrate carries at least one of said driver circuits thereon; and

attaching said divided glass substrate to a display substrate so that said driver circuit is electrically connected to said first electrodes through said transparent electrodes.

17. A method according to claim 16 further comprising a step of removing the divided glass substrate from said display substrate.

18. A method according to claim 16 wherein a thickness of said semiconductor islands is from 400 to 600Å.

19. A method according to claim 16 wherein said passivation film comprises silicon nitride.

20. A method according to claim 16 wherein said display device is a passive type liquid crystal device.

21. A method according to claim 16 wherein said display device is an active matrix type liquid crystal device.

22. A method of manufacturing a display device comprising:

preparing at least one display substrate provided with a plurality of first transparent electrodes;

forming a semiconductor film over a glass substrate;

crystallizing said semiconductor film;

patterning the crystallized semiconductor film into a plurality of semiconductor islands;

forming a plurality of thin film transistors with said semiconductor islands as an active layer thereof for constituting a plurality of driver circuits;

forming a passivation film over the plurality of thin film transistors;

forming second transparent electrodes over said passivation film wherein said transparent electrodes comprise a transparent conductive oxide;

dividing said glass substrate to obtain at least one divided glass substrate wherein said divided glass substrate carries at least one of said driver circuits thereon; and

attaching said divided glass substrate to a display substrate so that said driver circuit is electrically connected to said electrodes through said first and second transparent electrodes.

23. A method according to claim 22 wherein a thickness of said semiconductor islands is from 400 to 600Å.

24. A method according to claim 22 wherein said display device is a passive type liquid crystal device.

25. A method according to claim 22 further comprising a step of removing the divided glass substrate from said display substrate so that said driver circuit remains connected to said electrodes.

26. A method according to claim 22 wherein said display device is a passive type liquid crystal device.

27. A method according to claim 22 wherein said display device is an active matrix type liquid crystal device.

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